

General Description

FSMOS[®] MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially designed to use in motor control systems with driving voltage of more than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

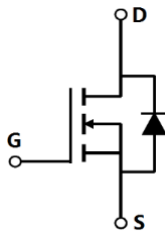
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$I_{D, pulse}$	320	A
$R_{DS(ON), max} @ V_{GS}=10V$	11	m Ω
Q_g	30	nC

Marking Information

Product Name	Package	Marking
SFS15R11DNF	TO252	SFS15R11DN

Package & Pin information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	150	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	80	A
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	320	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	80	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	320	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	170	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	280	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.87	$^\circ\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	150			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	3		4.5	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		9.6	11	m Ω	$V_{GS}=10\text{ V}, I_D=30\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=150\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	R_G		1.6		Ω	$f=1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1949		pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		719		pF	
Reverse transfer capacitance	C_{rss}		14		pF	
Turn-on delay time	$t_{d(on)}$		15		ns	$V_{GS}=10\text{ V}$, $V_{DS}=80\text{ V}$, $R_G=2\ \Omega$, $I_D=40\text{ A}$
Rise time	t_r		9		ns	
Turn-off delay time	$t_{d(off)}$		21		ns	
Fall time	t_f		9		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		30		nC	$V_{GS}=10\text{ V}$, $V_{DS}=80\text{ V}$, $I_D=40\text{ A}$
Gate-source charge	Q_{gs}		10		nC	
Gate-drain charge	Q_{gd}		10		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.1	V	$I_S=30\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		88		ns	$V_R=80\text{ V}$, $I_S=40\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		72		nC	
Peak reverse recovery current	I_{rrm}		1.6		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

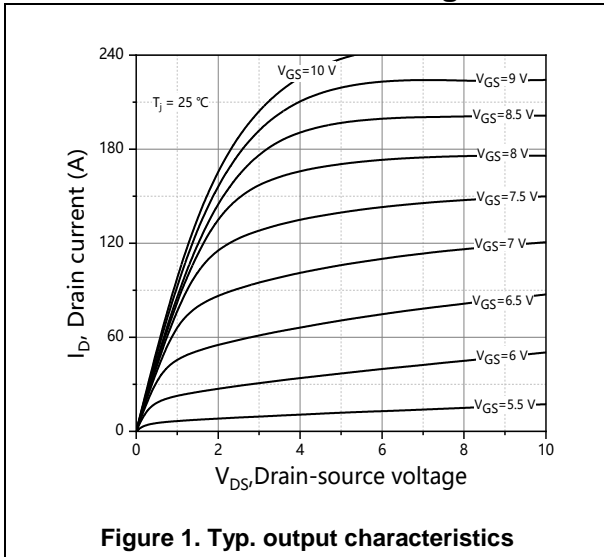


Figure 1. Typ. output characteristics

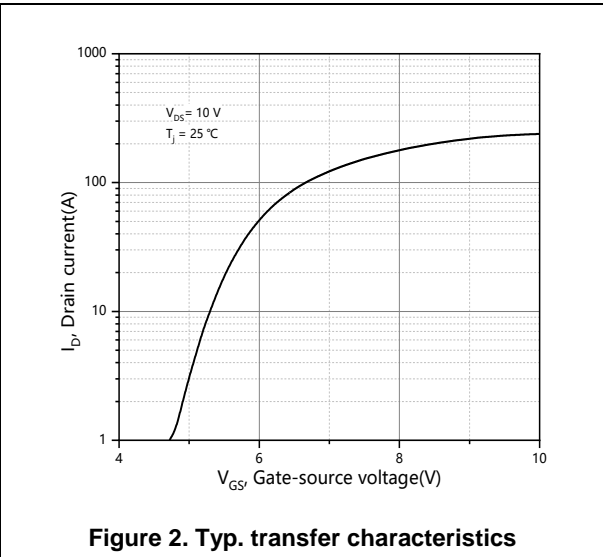


Figure 2. Typ. transfer characteristics

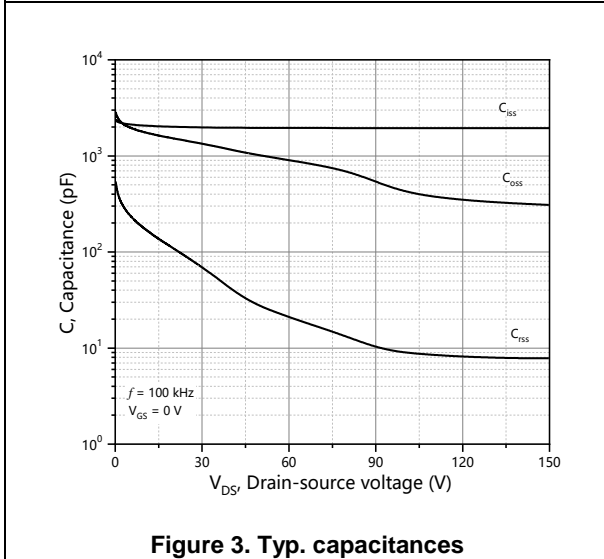


Figure 3. Typ. capacitances

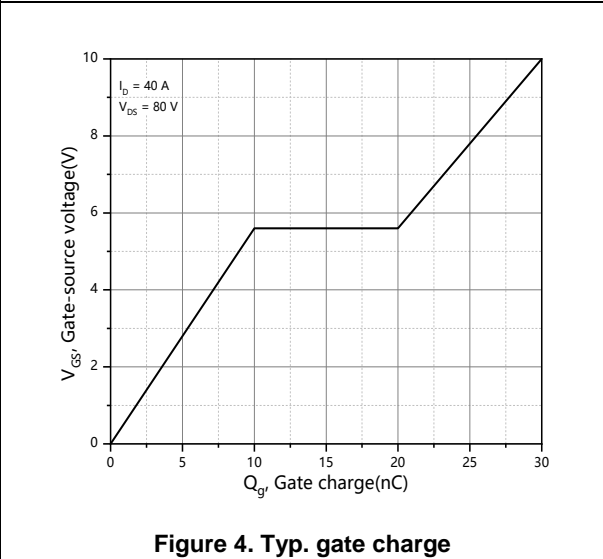


Figure 4. Typ. gate charge

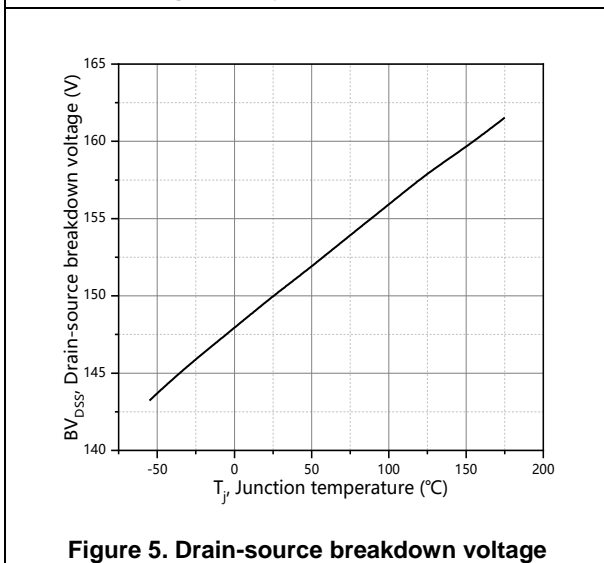


Figure 5. Drain-source breakdown voltage

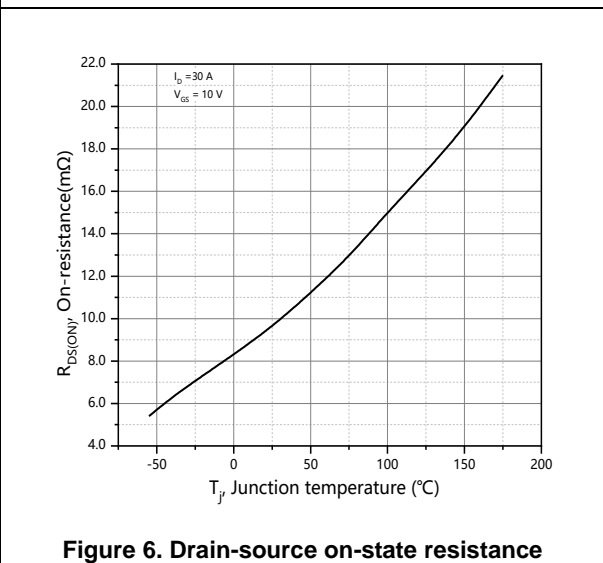
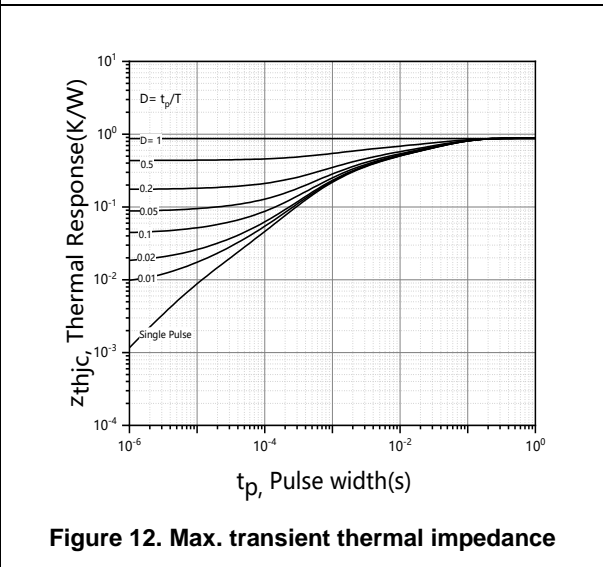
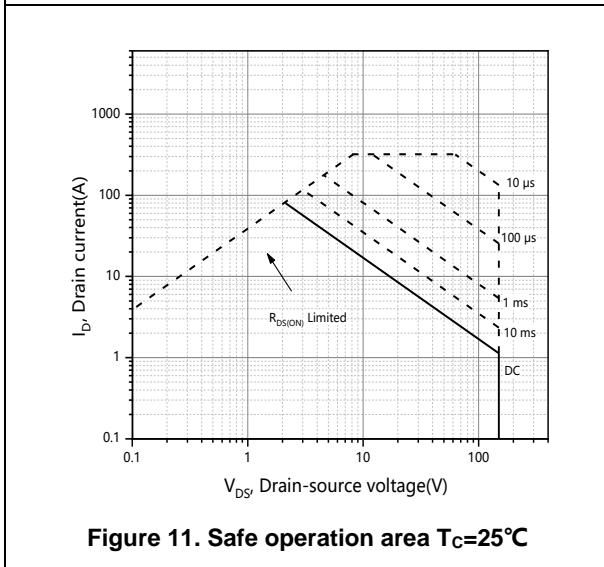
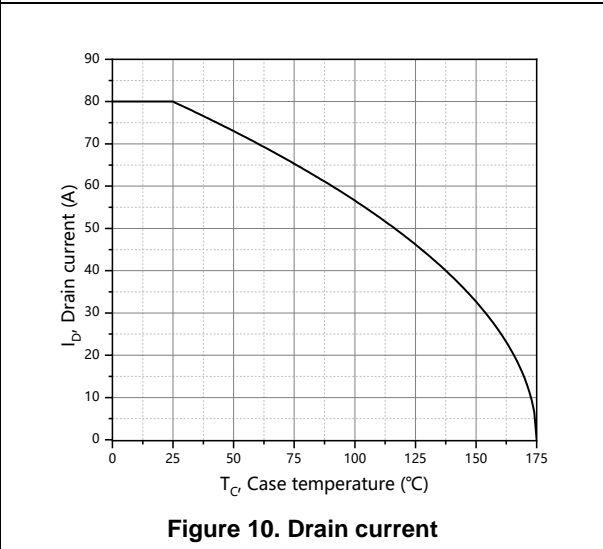
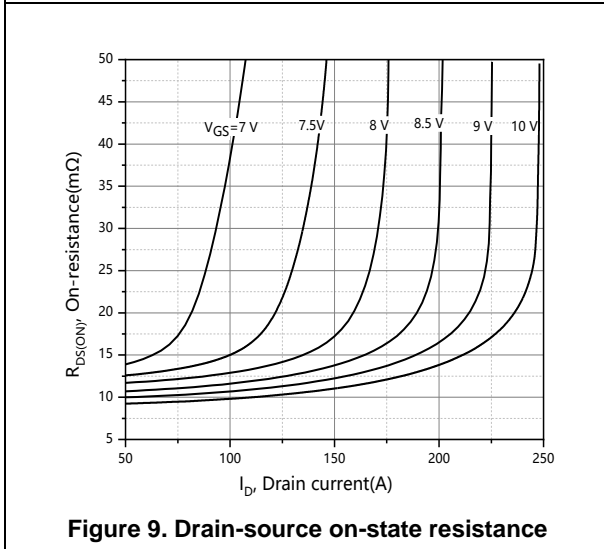
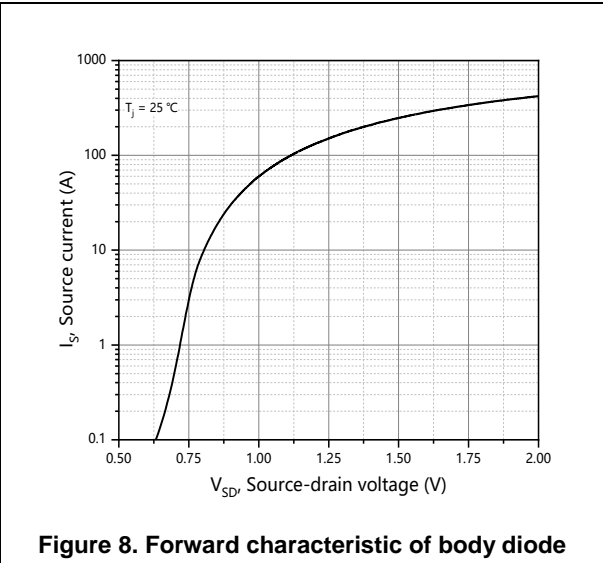
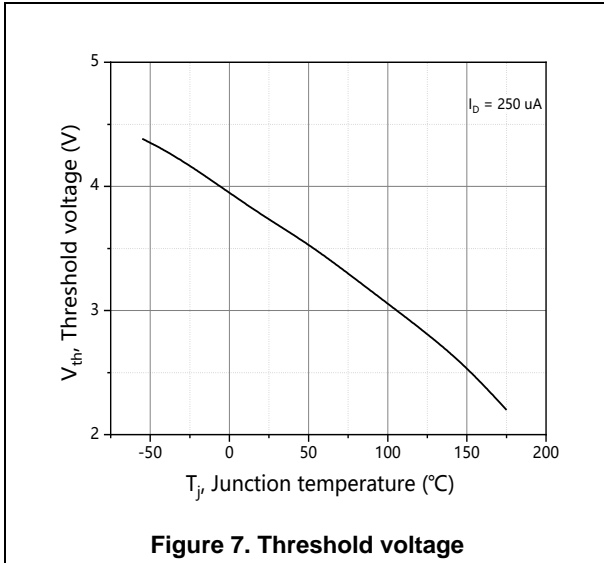


Figure 6. Drain-source on-state resistance



Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

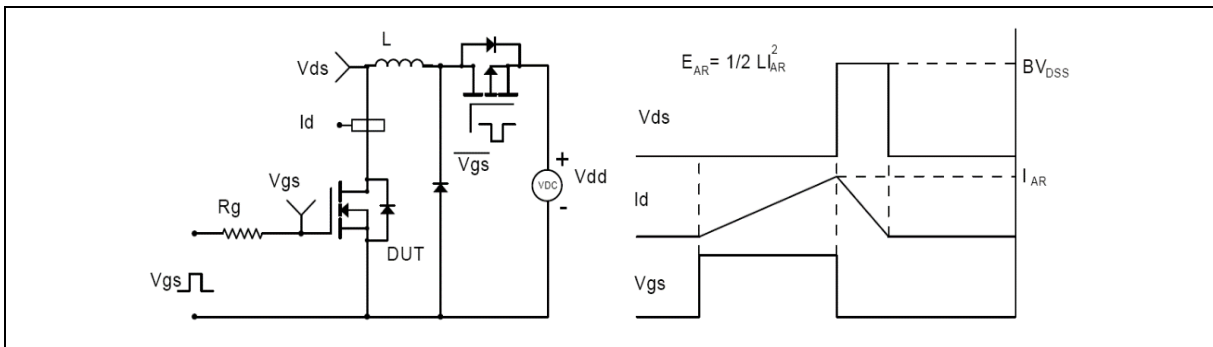
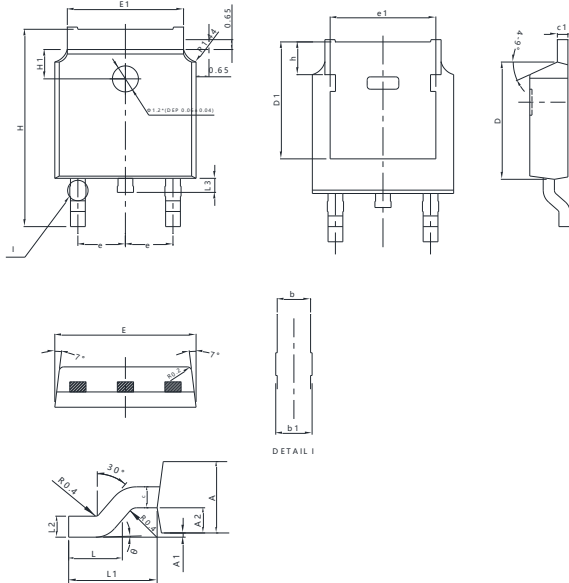


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.2	2.3	2.4
A1	0.00	0.075	0.15
A2	0.97	1.02	1.07
b	0.60	0.67	0.74
b1	0.65	-	1.15
c	0.508	0.528	0.548
c1	0.478	0.508	0.538
D	6.0	6.1	6.2
D1	5.15	5.25	5.35
E	6.5	6.6	6.7
E1	5.184	5.334	5.484
e	2.286BSC		
e1	4.806	4.826	4.846
H	9.8	10.0	10.2
H1	1.5	1.6	1.7
h	1.15	1.25	1.35
L	1.4	1.5	1.6
L1	2.888 REF		
L2	0.51BSC		
L3	0.80	0.90	1.00
θ	0°	-	10°

Version : TO252-G package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO252-G	2500	2	5000	6	30000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS15R11DNF	TO252	yes	yes	yes

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